2SD882

TO-126 Plastic-Encapsulate Transistors

FEATURES

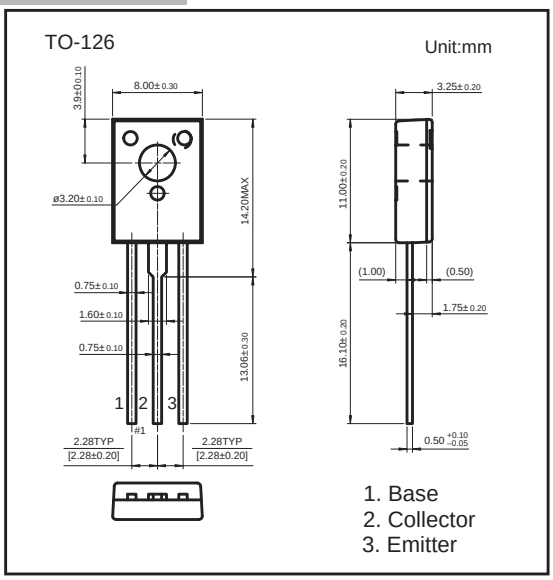
- Excellent hFE linearity and high hFE

hFE = 60 to 400 (VCE = 2 V, IC = 1 A)

- NPN Transistors

MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current to Continuous	I_C	3	A
Collector Dissipation	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

PACKAGE INFORMATION

Device	Package	Shipping
2SD882	TO-126	2000/Tape&Reel

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=100uA ,I_E=0	40			V
Collector-emitter breakdown voltage	V_{CEO}	I_C= 10 mA , I_B=0	30			V
Emitter-base breakdown voltage	V_{EBO}	I_E= 100 uA ,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=40 V , I_E=0			1	uA
Collector cut-off current	I_{CEO}	V_{CE}=30 V , I_B=0			10	uA
Emitter cut-off current	I_{EBO}	V_{EB}=6V , I_C=0			1	uA
DC current gain	h_{FE}	V_{CE}= 2V, I_C= 1A	60		400	
		V_{CE}=2V, I_C= 100mA	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=2A, I_B= 0.2A			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=2A, I_B= 0.2A			1.5	V
Transition frequency	f_T	V_{CE}=5 V, I_C=0.1mA,f = 10MHz	50			MHz

■ Classification of $h_{fe(1)}$

Type	2SD882-R	2SD882-Q	2SD882-P	2SD882-E
Range	60-120	100-200	160-320	200-400